



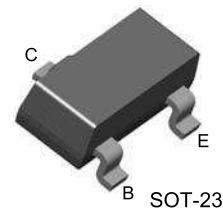
ON Semiconductor®

MMBT5401

PNP Epitaxial Silicon Transistor

Features

- PNP General-Purpose Amplifier
- This device is designed as a general-purpose amplifier and switch for applications requiring high voltage.



Ordering Information

Part Number	Marking	Package	Packing Method
MMBT5401	2L	SOT-23 3L	Tape and Reel, 3000 pcs, 7 inch Reel
MMBT5401-D87Z	2L	SOT-23 3L	Tape and Reel, 10000 pcs, 13 inch Reel

Absolute Maximum Ratings^{(1),(2)}

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{CBO}	Collector-Base Voltage	-160	V
V_{EBO}	Emitter-Base Voltage	-5.0	V
I_C	Collector Current - Continuous	-600	mA
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Notes:

1. These ratings are based on a maximum junction temperature of 150°C .
2. These are steady-state limits. ON Semiconductor should be consulted on applications involving pulsed or low-duty-cycle operations.